

Description

The SX85N08NF uses advanced technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 10V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

$V_{DS} = 85V$ $I_D = 85A$

$R_{DS(ON)} < 5.8m\Omega$ $V_{GS}=10V$

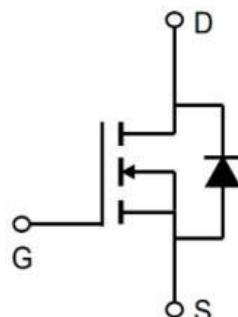
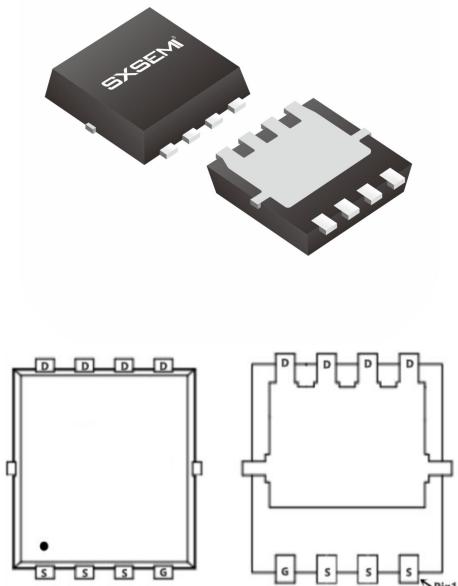
Application

Battery protection

Load switch

Uninterruptible power supply

PDFN5*6-8L



Absolute Maximum Ratings ($T_c=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	85	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D @ T_c=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	100	A
$I_D @ T_c=100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	86	A
IDM	Pulsed Drain Current	544	A
EAS	Single Pulse Avalanche Energy	434	mJ
$P_D @ T_c=25^\circ C$	Total Power Dissipation ⁴	166	W
T_{STG}	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C
$R_{\theta JA}$	Thermal Resistance Junction-Ambient	0.65	°C/W
$R_{\theta JC}$	Thermal Resistance Junction-Case	62.5	°C/W

Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V(BR)DSS	Drain-source breakdown voltage	$V_{GS}=0\text{V}, I_D=250\mu\text{A}$	85	91		V
VGS(th)	Gate threshold voltage	$V_{DS}=V_{GS}, I_D=250\mu\text{A} T_J=25^\circ\text{C}$	2.0	3.0	4.0	V
IDSS	Zero gate voltage drain current	$V_{DS}=80\text{V}, V_{GS}=0\text{V} T_J=25^\circ\text{C}$	-	-	1	μA
IDSS	Zero gate voltage drain current	$V_{DS}=80\text{V}, V_{GS}=0\text{V} T_J=125^\circ\text{C}$	-	-	- 5	μA
IGSS	Gate-source leakage current	$V_{GS}=20\text{V}, V_{DS}=0\text{V}$	-	-	100	nA
RDS(on)	Drain-source on-state resistance	$V_{GS}=10\text{V}, I_D=50\text{A}, T_J=25^\circ\text{C}$	-	4.8	5.8	$\text{m}\Omega$
gfs	Transconductance	$V_{DS}=5\text{V}, I_D=40\text{A}$	-	106	-	S
Ciss	Input Capacitance	$V_{GS}=0\text{V}, V_{DS}=40\text{V}, f=1\text{MHz}$	-	3503	-	pF
Coss	Output Capacitance		-	1048	-	pF
Crss	Reverse Transfer Capacitance		-	23	-	pF
QG	Gate Total Charge		-	82	-	nC
Qgs	Gate-Source charge	$V_{GS}=10\text{V}, V_{DS}=40\text{V}, I_D=20\text{A}$	-	15	-	nC
Qgd	Gate-Drain charge		-	33	-	nC
td(on)	Turn-on delay time		-	14.9	-	ns
tr	Rise time	$T_J=25^\circ\text{C}, V_{GS}=10\text{V}, V_{DS}=40\text{V}, R_L=3\Omega$	-	35	-	ns
td(off)	Turn-off delay time		-	50	-	ns
tr	Fall time		-	37	-	ns
R _G	Gate resistance	$V_{GS}=0\text{V}, V_{DS}=0\text{V}, f=1\text{MHz}$	-	2	-	Ω
VSD	Body Diode Forward Voltage	$V_{GS}=0\text{V}, I_{SD}=10\text{A}$	-	0.85	1.2	V
t _{rr}	Body Diode Reverse Recovery Time	$I=20\text{A}, dI/dt=100\text{A}/\mu\text{s}$	-	70	-	ns
Qrr	Body Diode Reverse Recovery Charge		-	61	-	nC

Note :

- 1、The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2、The data tested by pulsed , pulse width .The EAS data shows Max. rating .
- 3、The test cond \equiv 300us duty cycle \equiv 2%, duty cycle ition is $V_{DD}=64\text{V}$, $V_{GS}=10\text{V}$, $L=0.1\text{mH}$, $I_{AS}=53.8\text{A}$
- 4、The power dissipation is limited by 175°C junction temperature
- 5、The data is theoretically the same as ID and IDM , in real applications , should be limited by total power dissipation.

Typical Characteristics

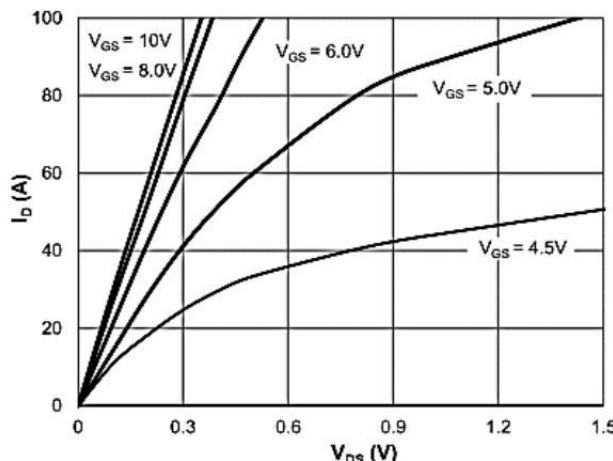


Figure 1: Saturation Characteristics

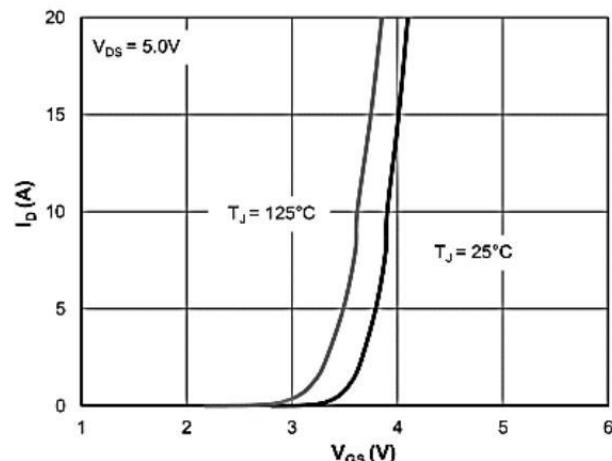


Figure 2: Transfer Characteristics

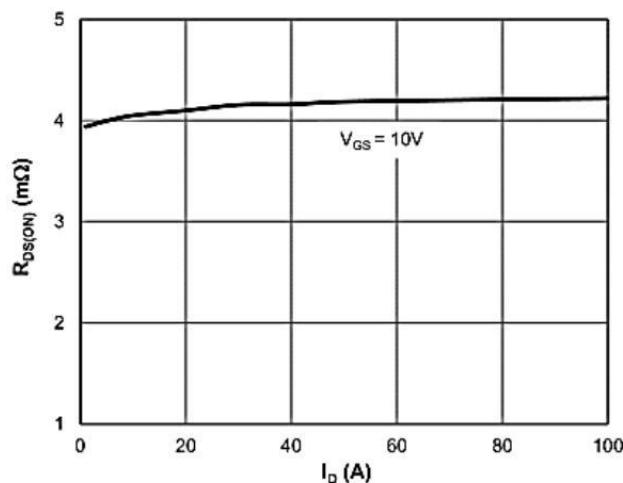
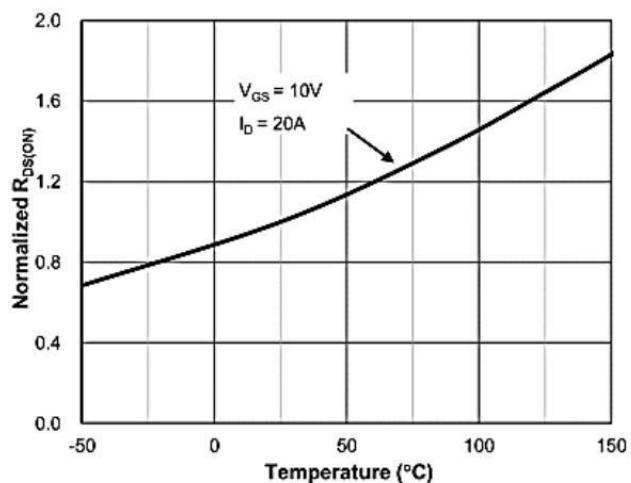
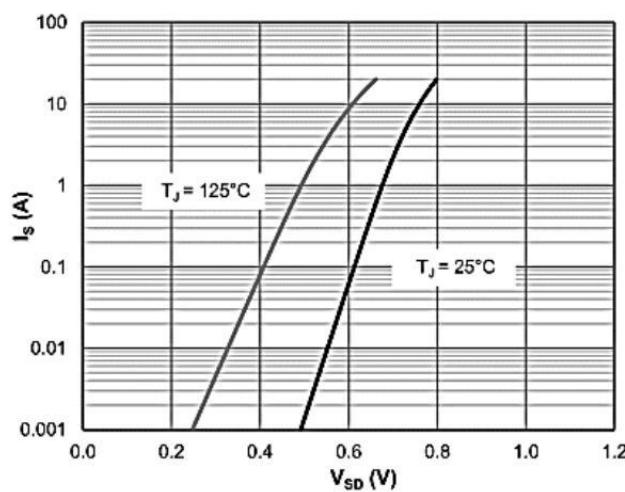
Figure 3: $R_{DS(\text{ON})}$ vs. Drain CurrentFigure 4: $R_{DS(\text{ON})}$ vs. Junction Temperature

Figure 7: Body-Diode Characteristics

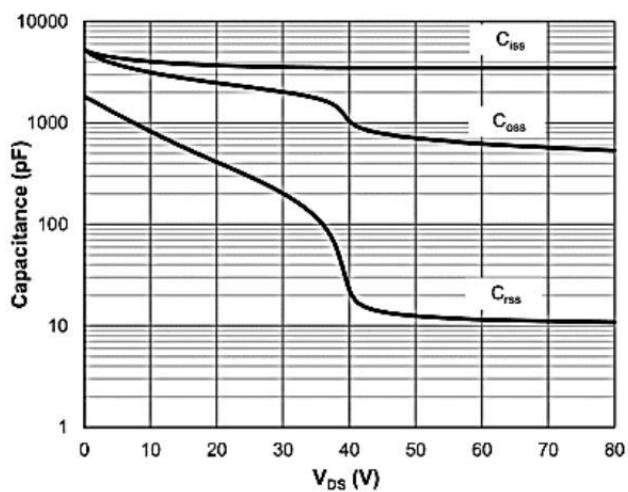


Figure 8: Capacitance Characteristics

Typical Characteristics

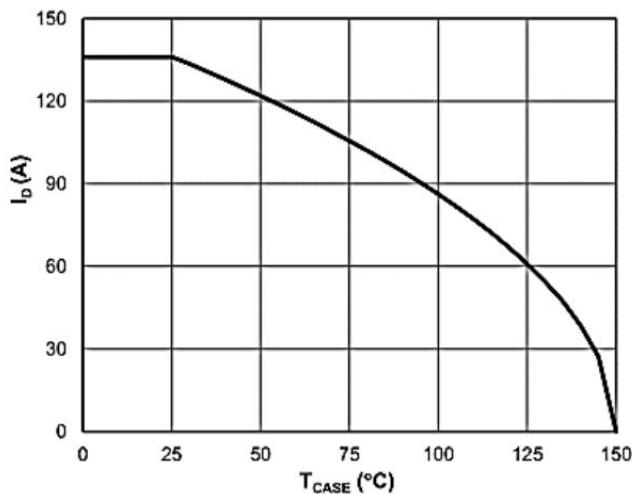


Figure 9: Current De-rating

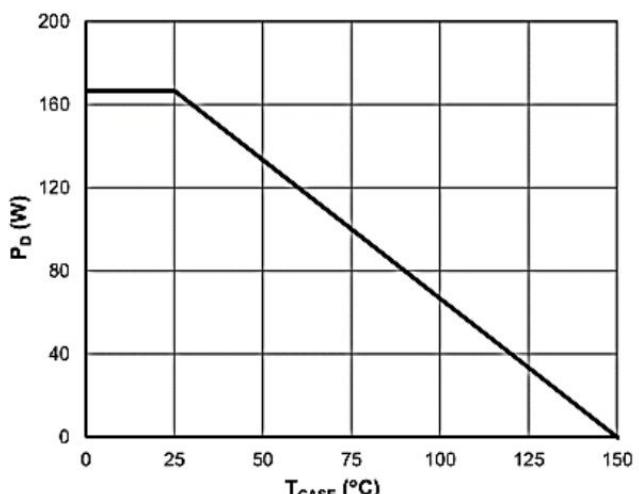


Figure 10: Power De-rating

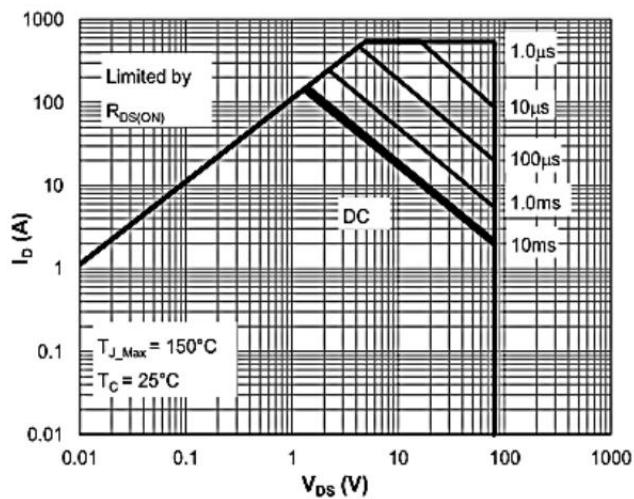


Figure 11: Maximum Safe Operating Area

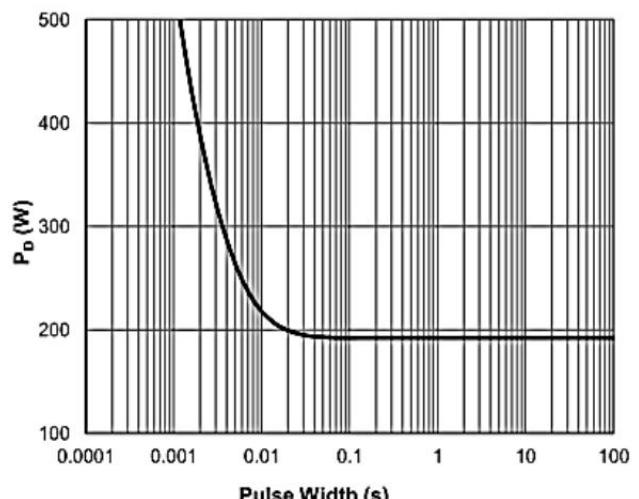


Figure 12: Single Pulse Power Rating, Junction-to-Case

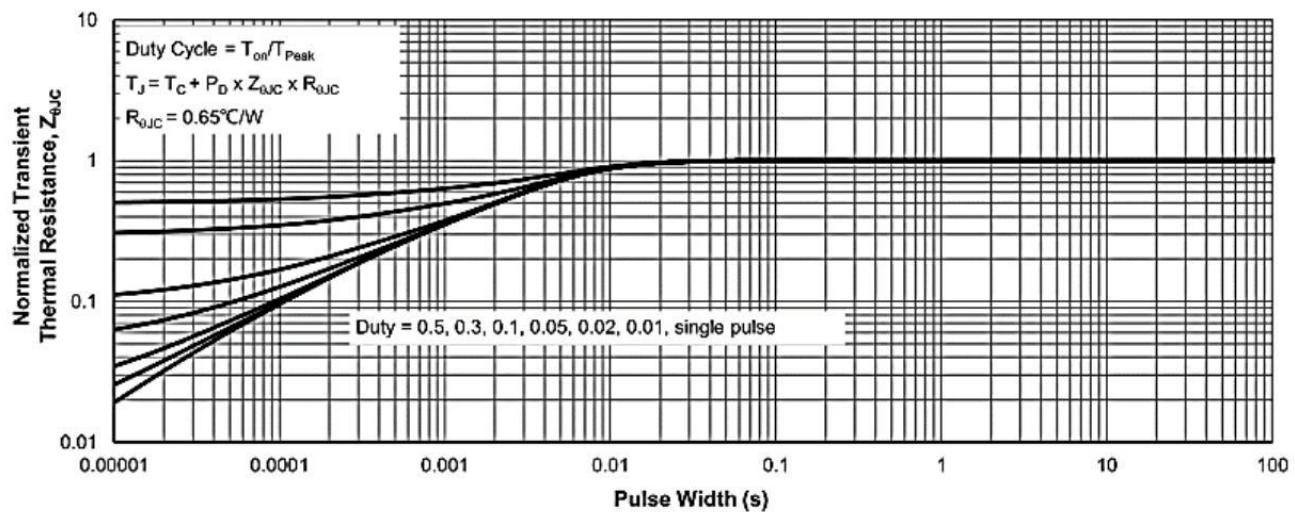
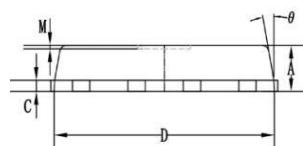
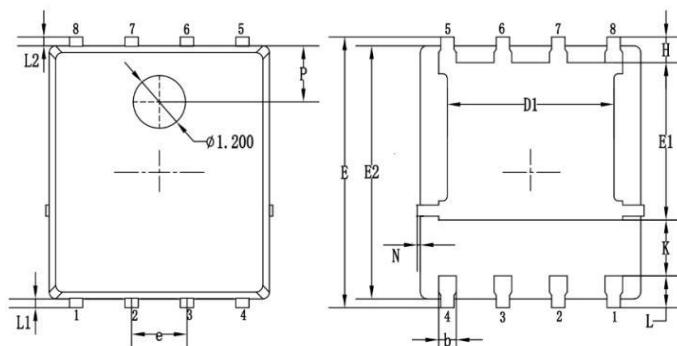


Figure 13: Normalized Maximum Transient Thermal Impedance

Package Mechanical Data-PDFN5*6-8L Single



Symbol	Dim in mm		
	Min	Typ	Max
A	0.9	1.05	1.2
b	0.3	0.4	0.5
C	0.2	0.25	0.35
D	4.9	5.05	5.2
D1	3.72	3.82	4.12
E	5.9	6.1	6.3
E1	3.3	3.5	3.7
E2	5.6	5.75	5.9
e	1.27BSC		
H	0.48	0.58	0.7
K	1.14	1.27	1.4
L	0.54	0.74	0.84
L1/L2	0.1	0.2	0.3
θ	8°	10°	12°
M	0.08REF		
N	0		0.15
P	1.28REF		

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
TAPING	PDFN5X6-8L		5000